FBAR 소자의 제작기법 및 공진특성

윤기완* · 송해일** · 이재영* · 마이린* · 휴메이윤 카비르*

Fabrication Techniques & Resonance Characteristics of FBAR Devices

Giwan Yoon* · Hae-il Song** · Jae-young Lee* · Linh Mai* · S. M. Humayun Kabir*

이 논문은 2007년도 지능형 RF 연구센타의 연구비를 지원받았음

요 약

박막음향공진기(FBAR) 기술은 현재의 실리콘 공정기술과 높은 집적화 가능성으로 인하여 차세대 RF 필터를 제작할 수 있는 매우 희망적인 기술로 최근에 큰 관심을 불러 일으켜 왔다. RF 필터는 기본적으로 여러 개의 FBAR 소자들을 직렬과 병렬로 연결된 형태로 구성되므로 그 필터의 특성은 각각의 FBAR 소자의 특성에 크게 의존하게 된다. 따라서 우수한 품질의 FBAR 소자를 제작하기 위해서는 우선적으로 소자 및 공정의 최적화 설계가 중요한다. 이러한 최적화 설계는 FBAR 소자 특성을 크게 향상 시킬 수 있게 되고, 궁극적으로 우수한 성능을 가진 FBAR 필터의 구현으로 이어지게 된다. 본 논문에서는, 이러한 FBAR 소자의 공진특성을 더욱 효과적으로 향상시킬 수 있는 방법들에 관한 연구결과를 고찰하고 논의한다.

ABSTRACT

Film bulk acoustic wave resonator (FBAR) technology has attracted a great attention as a promising technology to fabricate the next-generation RF filters mainly because the FBAR technology can be integrated with current Si processing. The RF filters are basically composed of several FBAR devices connected in parallel and in series, and their characteristics depend highly on the FBAR device characteristics. Thus, it is important to design high quality FBAR devices by device or process optimization. This kind of effort may enhance the FBAR device characteristics, eventually leading to FBAR filters of high performance. In this paper, we describe the methods to more effectively improve the resonance characteristics of the FBAR devices.

키워드
FBAR device, RF filter, resonance characteristics, quality factor

Ⅰ. Introduction

Recently, a considerable technology progress in microelectronics has enabled most of RF components to be highly integrated in a one-chip or a transceiver. Unfortunately, RF filters have been used as an off-chip component for wireless mobile systems. This is because the conventional RF filters can hardly be integrated with current Si-based CMOS process technologies [1-4]. From this point of view, the film bulk acoustic wave resonator (FBAR)

* 한국정보통신대학교
** Hynix

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devices and their technologies are likely to be a promising candidate to resolve the above issue mainly because the materials and fabrication process of FBAR device are very compatible with the current CMOS processing, leading to a fully integrated radio solution. Moreover, the FBAR devices have excellent characteristics such as high Q-factor, very small size, good power handling characteristic, and low insertion loss. In addition, the FBAR devices can be applied for RF/IF filters, duplexers, and voltage-controlled oscillators [5-8]. General acoustic wave devices based on piezoelectric materials have been in commercial use for over 60 years [9]. The ceramic resonators employ an electromagnetic wave and its size is also determined by the electromagnetic wavelength. Recalling the relationship (frequency x wavelength = speed), it will be clear that the acoustic phase velocity is approximately 3 to 4 orders-of-magnitude less than the electromagnetic phase velocity for a given resonance frequency. The dimensions of an acoustic wave device can be several orders of magnitude smaller than those for an electromagnetic wave device. Thus, the FBAR device has very small size, higher device performance, and stronger potential for realization of MMIC or one-chip than any other technology [10,11].

Ⅱ. Device Fabrication

As shown in Fig. 1, the thin film layers for the FBAR devices were deposited in an RF/DC magnetron sputtering system where four different materials (ZnO, SiO_2, W, and Co) were deposited. Besides, an electric dehydrate furnace was used to investigate the effects of various annealing methods on the FBAR characteristics. The acoustic Bragg reflector having SiO_2/W multilayers was formed by the thin-film deposition method on 4-inch silicon wafers. Each layer has one quarter wave-length (λ/4) of the resonance frequency in order to acoustically isolate the piezoelectric layer from the silicon substrate. In order to further improve the resonance characteristics of the FBAR devices, a thermal annealing process was additionally employed for the W/SiO_2 multi-layered Bragg reflectors immediately after they were deposited on a silicon substrate using an RF sputtering technique. In addition, the FBAR devices with the Bragg reflectors annealed at 400℃/30 min have shown excellent resonance characteristics in terms of return loss and Q-factor. Based on these findings, the optimum thermal annealing condition seems to be around 400℃/30 min and this approach seems very useful for improving the resonance characteristics of SMR-type FBAR devices with the multi-layer Bragg reflectors. Finally, the effects of the thermal annealing of the Bragg reflectors on the resonance characteristics of the FBAR devices particularly with Co electrodes were investigated and compared with those with Al electrodes. We fabricated the two devices, which are Al-FBAR and Co-FBAR devices for comparing their resonance characteristics. Compared with Al-FBAR devices, the resonance characteristics are more improved in Co-FBAR devices, indicating that the ZnO/Co has highly preferred orientation towards c-axis as compared to the ZnO/Al. Consequently, the resonance characteristics can be further improved by using Co electrodes, instead of using Al electrodes. The combination of both thermal annealing and Co electrodes seems very useful to more effectively improve the resonance characteristics of the FBAR devices with the W/SiO_2 multi-layer reflectors

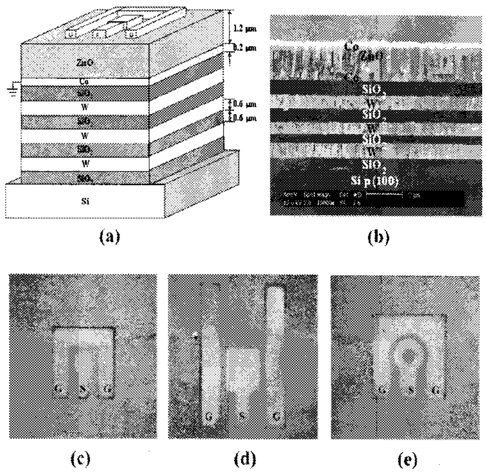

Fig. 1 (a) three-dimensional schematic, (b) cross section SEM picture, and three kinds of top-view patterns [(c) pattern 1, (d) pattern 2, and (e) pattern 3] of FBAR devices.

Ⅲ. Resonance Characteristics

Return loss (S_{11}) of three patterns were plotted and summarized for the comparison of the annealing effects according to three different annealing steps in Fig. 2 and Table 1. The resonance characteristics of the three samples annealed by Bragg reflector annealing, post-annealing, and two-step annealing were compared with the non-annealed sample. First, the return losses of sample B treated by Bragg reflector-annealing were around 3.18, 1.384, 0.96 dB better than those of non-annealed sample A. Second, the return losses of sample C were around 4.87, 4.244, 8.99 dB increased by post-annealing than those of non-annealed sample A. Last, the return losses of sample D were around 10.37, 11.614, 12.81 dB increased by proposed two-step annealing. Therefore, the addition of the post-annealing of 200℃/2 hours on the sample D that is already annealed by Bragg reflector-annealing at 400℃/30 min might further eliminate any imperfect microstructures and incomplete adhesions in FBAR devices without any significant degradation in the acoustic Bragg reflector.

To estimate the resonator performance, effective electromechanical coupling coefficient and series/parallel quality factors are used as figure of merits (FOMs).

$$K_{eff}^2 = \left(\frac{\pi}{2}\right)^2 \frac{f_p - f_s}{f_p}$$

$$Q_{s/p} = \frac{f_{s/p}}{2}\left|\frac{d\angle Z_{IN}}{df_{s/p}}\right|_{f_{s/p}}$$

where f_S and f_P are series and parallel resonance frequencies and the $\angle Z_{in}$ is the slope of the input impedance phase. Fig. 3 shows that the slop of $\angle Z_{in}$ as a function of the frequency with the pattern 1 in Fig. 2 and the calculated effective electromechanical coupling coefficient K_{eff}^2 and series and parallel quality factor $Q_{S/P}$ values for FBAR devices with pattern 1 are tabulated in Table 2.

K_{eff}^2 and $Q_{S/P}$ of the RBAR resonators annealed by Bragg reflector-annealing and post-annealing methods were improved. Much more improvement could be obtained by

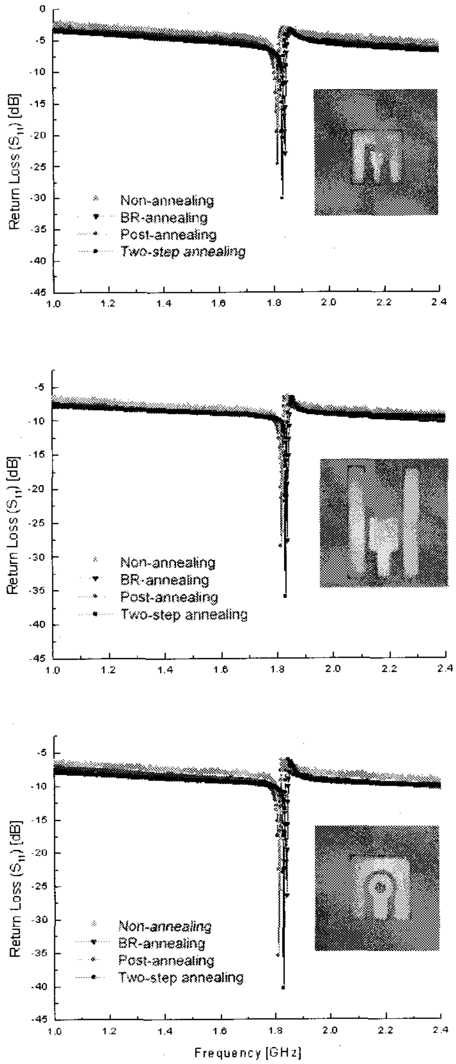

Fig. 2 Return loss S11 measurement results against frequency for three different top electrode patterns.

the proposed two-step annealing. The resonance characteristics were compared for various annealing methods. As a result, return loss S_{11}, series and parallel quality factor $Q_{S/P}$, and effective electromechanical coupling coefficient K_{eff}^2 could be significantly improved by two-step annealing.

Table 1. Summarized return loss measurement results for three different patterns.

Sample Name	Return loss [dB]		
	Pattern 1	Pattern 2	Pattern 3
Sample A	-14.79	-16.32	-17.48
Sample B	-17.97	-17.70	-18.44
Sample C	-19.66	-20.56	-26.47
Sample D	-25.16	-27.93	-30.29

Table 2. Calculated series and parallel quality factors and electromechanical coupling coefficients for FBAR devices (pattern 1).

Sample Name	Quality factor		Effective electromechanical coupling coefficient
	Q_s	Q_p	K_{eff}^2
Sample A	5266	5992	1.48%
Sample B	5337	6046	1.86%
Sample C	5775	7314	1.89%
Sample D	8391	7482	2.01%

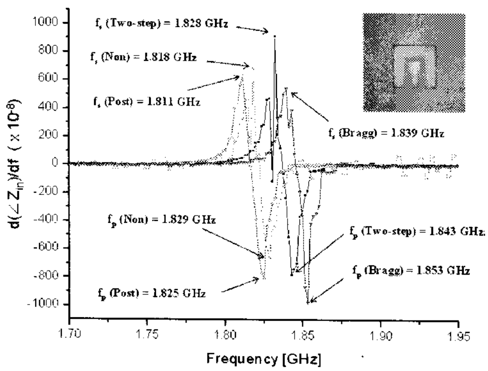

Fig. 3 Slopes of $\angle Z_{in}$ as a function of the frequency for different annealing conditions (FBAR devices with the pattern 1).

Ⅳ. Conclusion

In this paper, some methods to more effectively improve the resonance characteristics of the FBAR devices were clearly described. And, their resonance characteristics could be further enhanced by the optimization of the fabrication processing.

Acknowledgement

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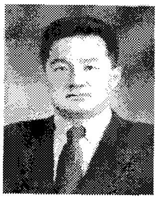
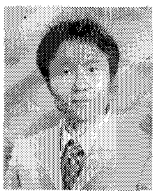
저자소개

Giwan Yoon



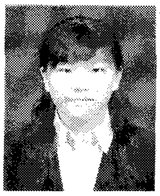
Member of KIMICS. Received BS degree in Seoul National University (SNU), Korea in 1983, MS in KAIST, Korea in 1985, and PhD in The University of Texas at Austin, USA in 1994. From 1985 to 1990, he was an engineer of LG Group. From 1994 to 1997, he was a senior engineer of Digital Equipment Corporation, USA. Currently, he is a professor of Information & Communications University (ICU), Daejeon, Korea.

Hae-il Song



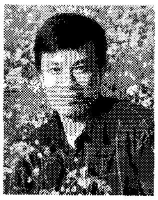
Received BS degree in Chungnam National University (CNU), Korea in 2003. From 2003 to 2005, he was an MS student, Information & Communications University (ICU), Daejeon, Korea. Currently, he is an engineer of Hynix Semiconductor. His research areas include nano-scaled semiconductor & RF MEMS devices.

Jae-young Lee



Member of KIMICS. Received BS degree in Information technology, Soon Chun Hyang University (SCH) in 2006. Since 2006, she has been an MS student, Information & Communications University (ICU), Daejeon, Korea. Her research areas include RF devices & designs and related technologies.

Linh Mai



Member of KIMICS. Received BS degree in Natural Science, Hanoi University, Vietnam in 1996. MS in ITIMS, Hanoi, Vietnam in 1998. From 1998 to 2001, he was a teacher of Posts and Telecommunications Institute of Technology(PTIT), Vietnam. Since 2001, he has been a PhD student, Information & Communications University (ICU), Daejeon, Korea. His research areas include nanoscaled solid-state devices & FBAR filter technology.

S. M. Humayun Kabir

Member of KIMICS. Received BS degree in Computer Science & Engineering, Khulna University, Bangladesh, in 2007. Since then, he has been an MS student in Communication & Electronics Lab (CEL), Information & Communications University (ICU), Daejeon, Korea. The research areas of interest include intelligent algorithms, space-time coding and MIMO systems.